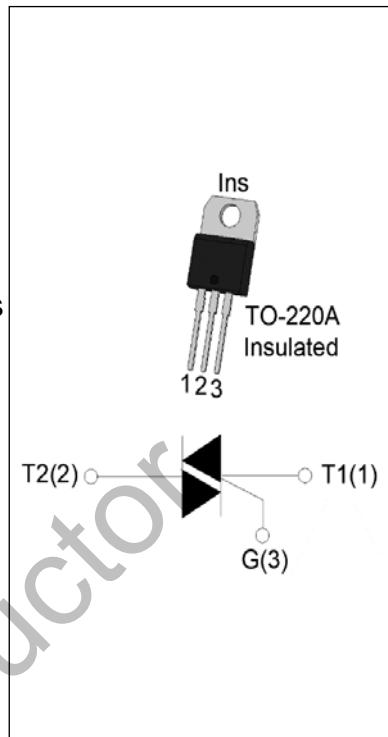


DESCRIPTION:

The BTA06-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. BTA06-800CW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, BTA06-800CW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\text{ I/II/III}}$	35/35/35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 100^\circ\text{C}$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	65	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		72	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	21	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{PP}	3	kV
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ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II -III	MAX.	35	mA
V _{GT}		I - II -III	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ		MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III	MAX.	50	mA
		II		60	
I _H	I _T =100mA		MAX.	35	mA
dV/dt	V _D =540V Gate Open T _j =125°C		MIN.	1200	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T _j =125°C		MIN.	4	A/ms
t _{on}	I _G =40mA I _A =200mA I _R =20mA T _j =25°C	TYP.	3	μs	
t _{off}			30		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit	
V _{TM}	I _{TM} =8.5A	t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage		T _j =125°C	0.82	V
R _D	Dynamic resistance		T _j =125°C	57	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C		5	μA
I _{RRM}		T _j =125°C		0.3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	3	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W

FIG.1 Maximum power dissipation versus RMS on-state current

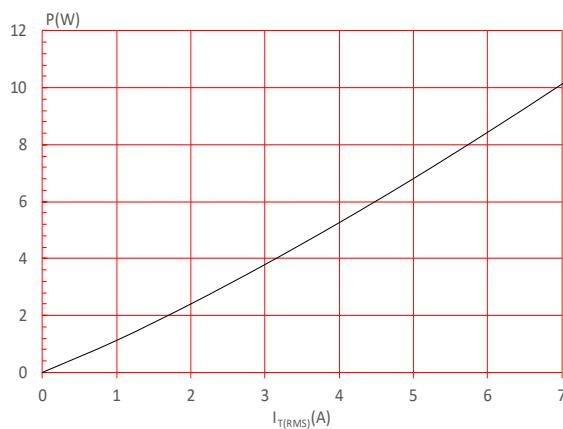


FIG.3: Surge peak on-state current versus number of cycles

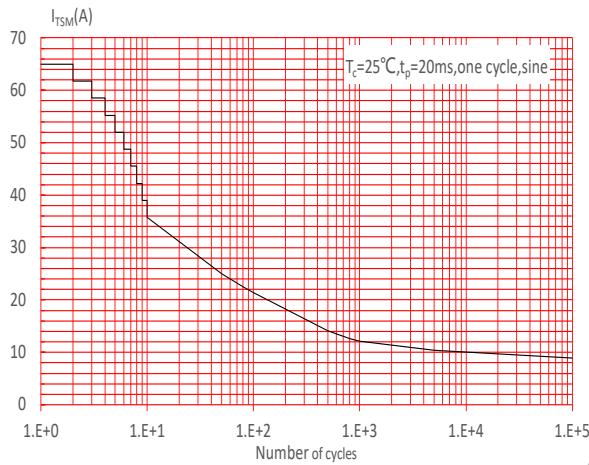


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

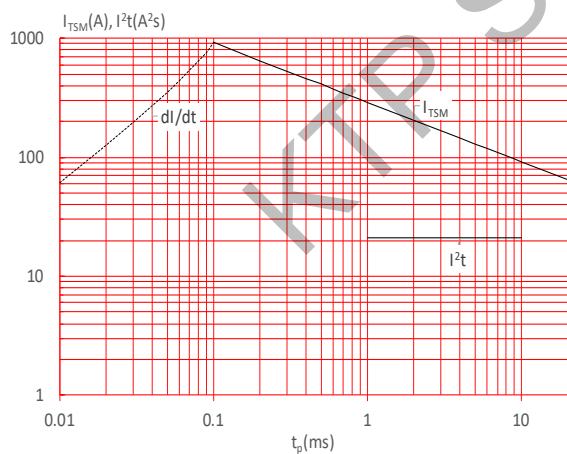


FIG.2: RMS on-state current versus case temperature

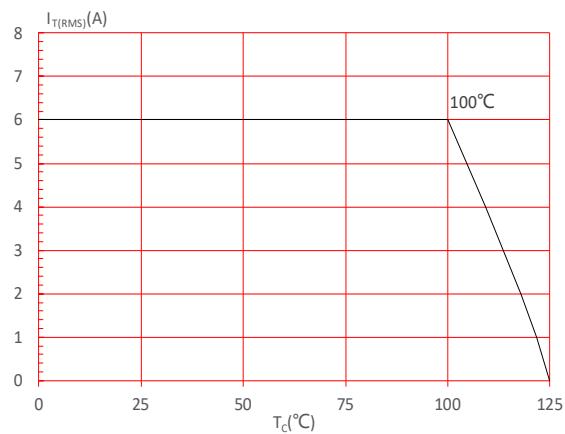


FIG.4: On-state characteristics

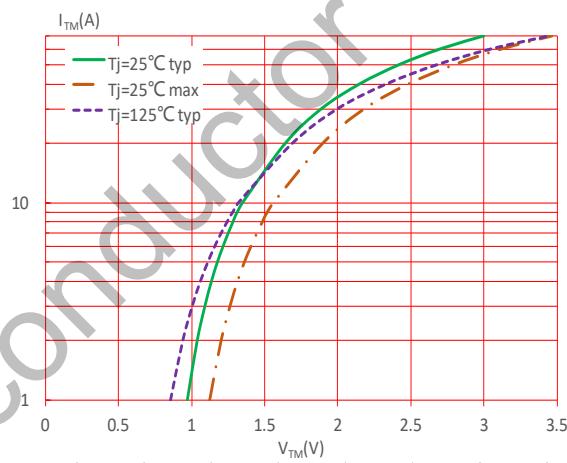


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

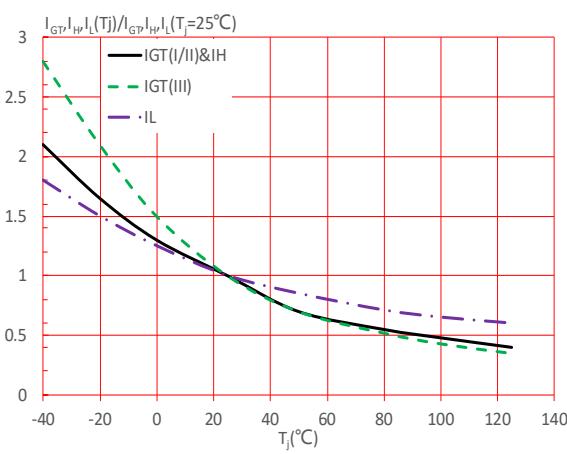
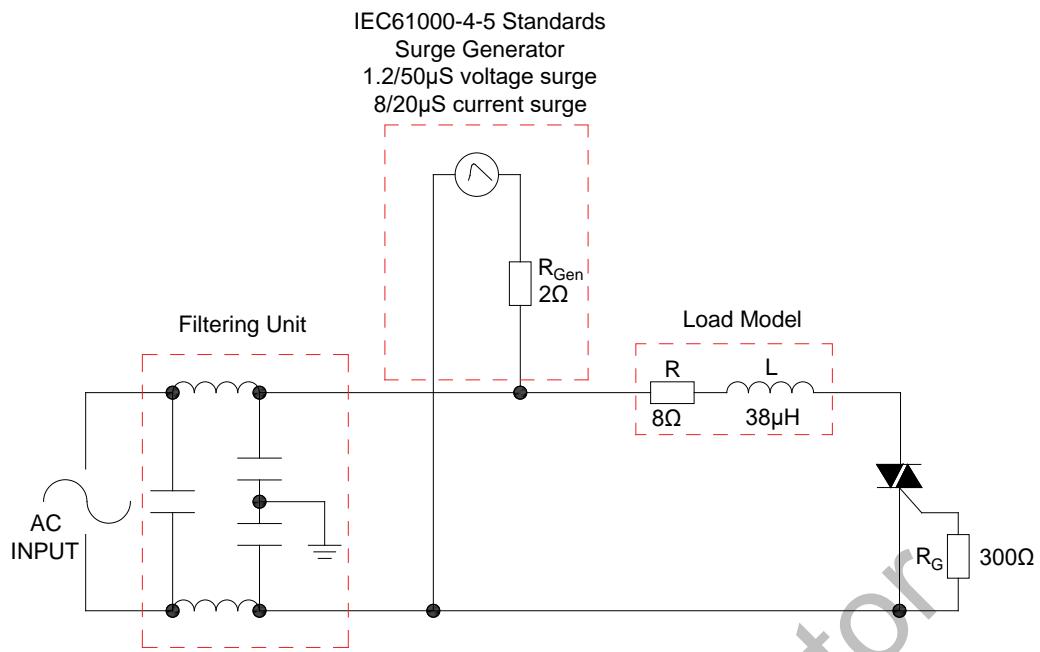
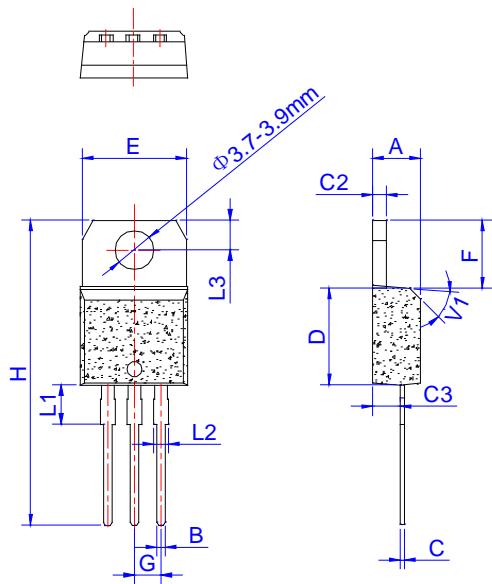


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

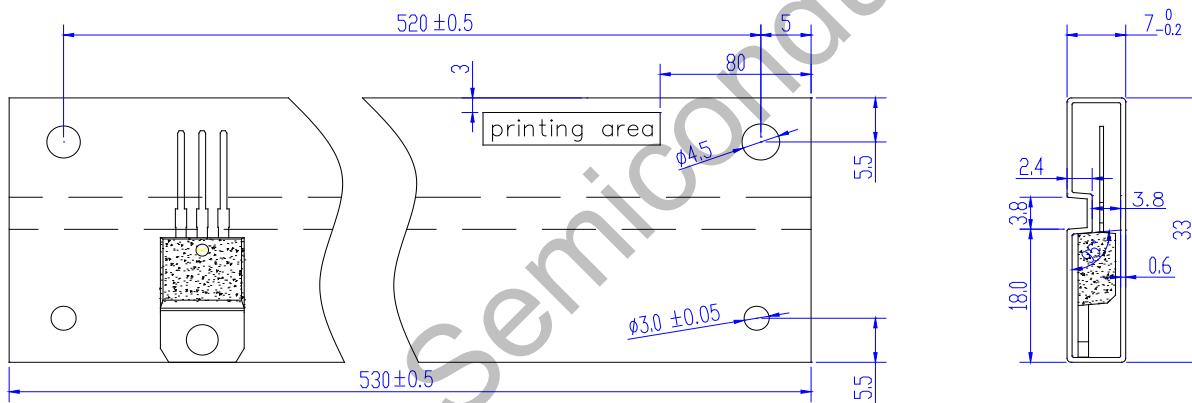


PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000